

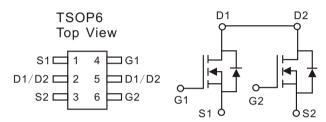
## Dual N-Channel 20V(D-S) MOSFET

These miniature surface mount MOSFET utilize High Cell Density process. Low RDS(on) assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are DC-DC converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

· Low RDS(o	n) Provides	Higher	Efficiency	and
Extends	Battery Lif	e		

- · Low gate charge 7nC
- · High performance
- · High current handling
- · Miniature TSOP-6 Surface Mount Package Saves Board Space

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (ohm)	Id(A)		
20	0.023 @ V <sub>GS</sub> = 4.5V	6.0		
20	0.033 @ V <sub>GS</sub> = 2.5V	5.2		



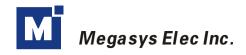
ABSOLUTE MAXIMUM RATINGS (TA = 25°C UNLESS OTHERWISE NOTED)					
Parameter			Maximum	Units	
Drain-Source Voltage		VDS	20	V	
Gate-Source Voltage			± 10		
Continuous Drain Current a	T <sub>A</sub> =25℃	l <sub>D</sub>	5.8		
Continuous Drain Current	T <sub>A</sub> =70℃	ID	3.7	А	
Pulsed Drain Current b		Ідм	10		
Continuous Source Current (Diode Conduction) a			0.46	Α	
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25℃	P <sub>D</sub>	1.25	W	
1 ower bissipation	T <sub>A</sub> =70℃	Fυ	0.8		
Operating Junction and Storage Temperature Range			-55 to 150	$^{\circ}$	

THERMAL RESISTANCE RATINGS				
Parameter			Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	t<= 5 sec	Втнја	100	°C/W
Maximum Junction-to-Ambient	Steady-State	ПІНЈА	166	

Notes: a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (TA = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	Limits			Units	
Parameter	Syllibol	lest Conditions	Min	Тур	Max	Units	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	Vgs=0V,ID=250uA	20				
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	0.5	0.80	1.5	V	
Gate-Body Leakage	Igss	V <sub>DS</sub> =0V,V <sub>GS</sub> = ± 10V			± 100	nA	
Zana Oata Walkana Duain O	Ipss	V <sub>DS</sub> =16V,V <sub>GS</sub> =0V			1	uA	
Zero Gate Voltage Drain Current	1055	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V,T <sub>J</sub> =55°C			10		
On–State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> =5V,V <sub>GS</sub> =4.5V	10			Α	
Dunin Course On Besistance	RDS(on)	Vgs=4.5V,lp=6.0A	20	23	26	mΩ	
Drain-Source On-Resistance <sup>a</sup>		Vgs=2.5 V, Ip=5.2A	30	33	37		
Forward Tranconductancea	<b>g</b> fs	VDS=5V,ID=3.0A		11		S	
Diode Forward Voltage	VsD	Is=2.00A,Vgs=0V		0.80	1.20	V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg			11			
Gate-Source Charge	Qgs	V <sub>DS</sub> =10V,V <sub>GS</sub> =4.5V I <sub>D</sub> =4.0 A		2.20		nC	
Gate-Drain Charge	Qgd	10 = 4.0 A		2.50		ı	
Switching							
Turn-On Delay Time	t <sub>d(on)</sub>			9	17		
Rise Time	tr	VDD=10V, ID=1A, RG=10 ohm, VGEN=4.5V		11	18	nc	
Turn-Off Delay Time	td(off)	1.5.75 57.11.1, 1.5.1		18	29	ns	
Fall-Time	tf			5	10		

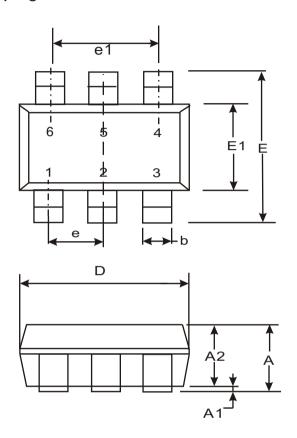
Notes: a. Pulse test: PW <= 300us duty cycle <= 2%.

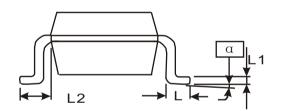
b. Guaranteed by design, not subject to production testing.

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## **Packaging Information**

TSOP-6





Dim	Millimeters		Inches		
ווווט	Min.	Max.	Min.	Max.	
Α	0.95	1.45 0.037		0.057	
A1	0.05	0.15	0.002	0.006	
A2	0.90	1.30	0.035	0.051	
b	0.35	0.55	0.0138	0.0217	
D	2.8	3.00	0.110	0.118	
Е	2.6	3.00	0.102	0.118	
E1	1.5	1.70	0.059	0.067	
е	0.95		0.037		
e1	1.90		0.075		
L	0.35	0.55	0.014	0.022	
L1	0.20BSC		0.008BSC		
L2	0.5	0.7	0.020	0.028	
α	0°	10°	0°	10°	